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Substitute for form 1449A/PTO	Application Number	10/759,081	RECEIVED
INFORMATION DISCLOSURE	Filing Date	January 20, 2004	CENTRAL FAX CENTER
STATEMENT BY APPLICANT	First Named Inventor	Dr. Chou H. Li	NOV 0 1 2006
	Group Art Unit	2815	
	Examiner Name	William F. Kraig	
Sheet 1 of 5	Attorney Docket Number	2480.202	

		U.S. Patent	Document	ENT DOCUMENTS	
Examiner Initials*	Cite No.'	Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
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^{&#}x27;Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code. ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁸Applicant is to place a check mark here if English language translation is attached. A8 indicates that only an English language abstract is attached.

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PAGE 9/18 * RCVD AT 11/1/2006 11:23:15 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-1/9 * DNIS:2738300 * CSID:16106803853 * DURATION (mm-ss):05-18

^{&#}x27;Unique citation designation number. ²See attached Kinds of U.S. Parent Documents. ⁸Enter Office that issued the document, by the two-letter code. ⁴For Japanese parent documents, the indication of the year of the reign of the Emperor must procede the serial number of the parent document. ⁶Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST, 16 if possible. ⁶Applicant is to place a check mark nere it English language translation is attached. AB indicates that only an English language abstract is attached.

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	Examiner Name	William F. Kraig	
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	Examiner Name	William F. Kralg	
Sheet 4 of 5	Attorney Docket Number	2480.202	

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Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), fittle of the article (when appropriate), title of the Item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published	T ²
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Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
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